

AOS Semiconductor Product Reliability Report

AO4822/AO4822L, rev B

Plastic Encapsulated Device

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This AOS product reliability report summarizes the qualification result for AO4822. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4822 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AO4822 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. Standard Product AO4822 is Pb-free (meets ROHS & Sony 259 specifications). AO4822L is a Green Product ordering option. AO4822 and AO4822L are electrically identical.

Absolute Maximum Ratings T _A =25°C unless otherwise noted						
Parameter Drain-Source Voltage Gate-Source Voltage		Symbol	Maximum	Units		
		V _{DS}	30	V		
		V_{GS}	±20	V		
Continuous Drain	T _A =25°C		8.5			
Current	T _A =70°C	I _D	6.6	Α		
Pulsed Drain Current		I _{DM}	30			
	T _A =25°C	P _D	2	W		
Power Dissipation T _A =70		r _D	1.28	VV		
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C		

Thermal Characteristics								
Parameter	Symbol	Тур	Max	Units				
Maximum Junction-to- Ambient	t ≤ 10s	Б	48	62.5	°C/W			
Maximum Junction-to- Ambient	Steady- State	$R_{ heta JA}$	74	110	°C/W			
Maximum Junction-to-Lead	Steady- State	$R_{ hetaJL}$	35	40	°C/W			



II. Die / Package Information:

AO4822L (Green Compound)

ProcessStandard sub-micronStandard sub-micron

low voltage N channel process low voltage N channel process

Package Type 8 leads SOIC 8 leads SOIC

Lead Frame Copper with Solder Plate Copper with Solder Plate

Die AttachAg epoxyAg epoxyBond wireAu 2milsAu 2 mils

Mold Material Epoxy resin with silica filler Epoxy resin with silica filler

Filler % (Spherical/Flake)90/10100/0Flammability RatingUL-94 V-0UL-94 V-0Backside MetallizationTi / Ni / AgTi / Ni / AgMoisture LevelUp to Level 1 *Up to Level 1*

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4822 (Standard) & AO4822L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°c Green: 168hr 85°c /85RH +3 cycle reflow@260°c	0hr	Standard: 49 lots Green: 16 lots	9625 pcs	0
НТСВ	Temp = 150°c , Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	13 lots (note A*)	1066 pcs 77+5 pcs / lot	0
HTRB	Temp = 150°c , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	13 lots (note A*)	1066 pcs 77+5 pcs / lot	0
HAST	130 +/- 2°c , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 33 lots Green: 13 lots (note B**)	2530 pcs 50+5 pcs / lot	0
Pressure Pot	121°c , 29.7 psi, RH=100%	96 hrs	Standard: 49 lots Green: 16 lots (note B**)	3575 pcs 50+5 pcs / lot	0
Temperature Cycle	-65°c to 150°c, air to air, 0.5hr per cycle	250 / 500 cycles	Standard: 49 lots Green: 15 lots (note B**)	3520 pcs 50+5 pcs / lot	0



III. Result of Reliability Stress for AO4822 (Standard) & AO4822L (Green) Continues

DPA	Internal Vision	NA	5	5	0
	Cross-section		5	5	
	X-ray		5	5	
CSAM		NA	5	5	0
Bond Integrity	Room Temp	0hr	40	40 wires	0
3 .,	150°c bake	250hr	40	40 wires	
	150°c bake	500hr	40	40 wires	
Solderability	230°c	5 sec	15	15 leads	0
Die shear	150°c	0hr	10	10	0

Note A: The HTGB and HTRB reliability data presents total of available AO4822 and AO4822L burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO4822 and AO4822L comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 3.3 MTTF = 34592 years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4822). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9 / [2 (N) (H) (Af)]$

= 1.83 x 10^9 / [2 (6×164) (168) (258)+2 (3×164) (500) (258)+2 (4×164) (1000) (258)] = 3.3 **MTTF** = 10^9 / FIT = 3.03 x 10^8 hrs = 34592 years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval **N** = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = Exp [Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K



V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual. Guaranteed Outgoing Defect Rate: **< 25 ppm** Quality Sample Plan: conform to **Mil-Std-105D**